

# **Applying Co-Sputtering to Increase DDR During Deposition of Titanium Oxides and Silicon Oxides**

J. Kazuss, V.Kozlov, E.Machevskis  
SIDRABE Inc, Riga, Latvia

# Problems of vacuum coatings technology

- Quality
- Productivity
- Cost

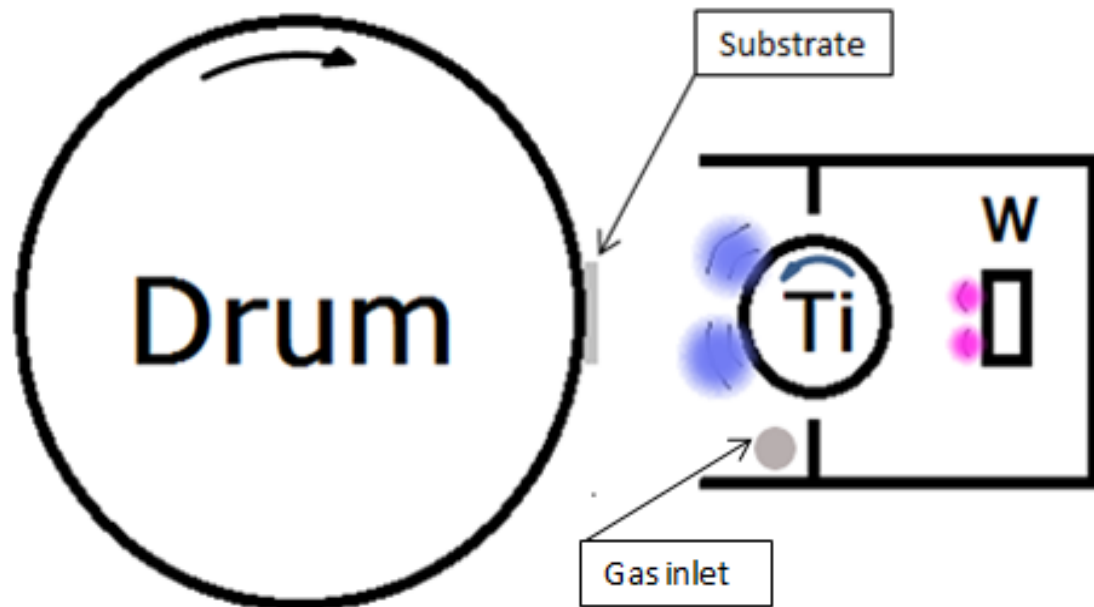
# How reach increase of technology productivity?

- Increase in specific power of sputtering ( $w/m$ ).
- Work in a transition mode with control on a feedback.
- Increase in sputtering factor by consecutive co-sputtering.

<b>Material</b>	<b>DDR, co-sputtering</b>
$\text{Al}_2\text{O}_3$	+80%
$\text{TiO}_2$	+100%
C	+280%
$\text{SiO}_2$	??

Data from Fraunhofer institute publications

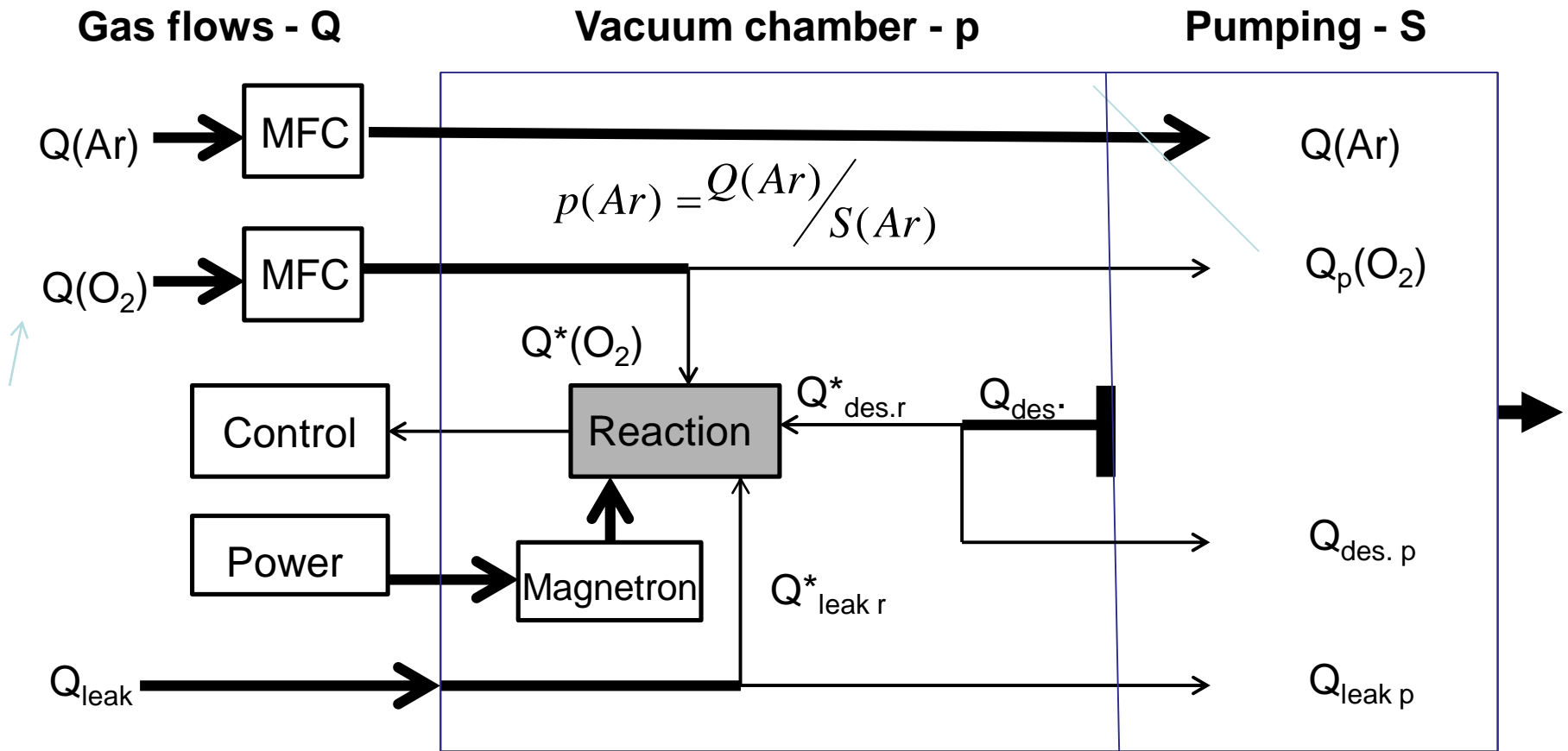
## Serial co-sputtering diagram

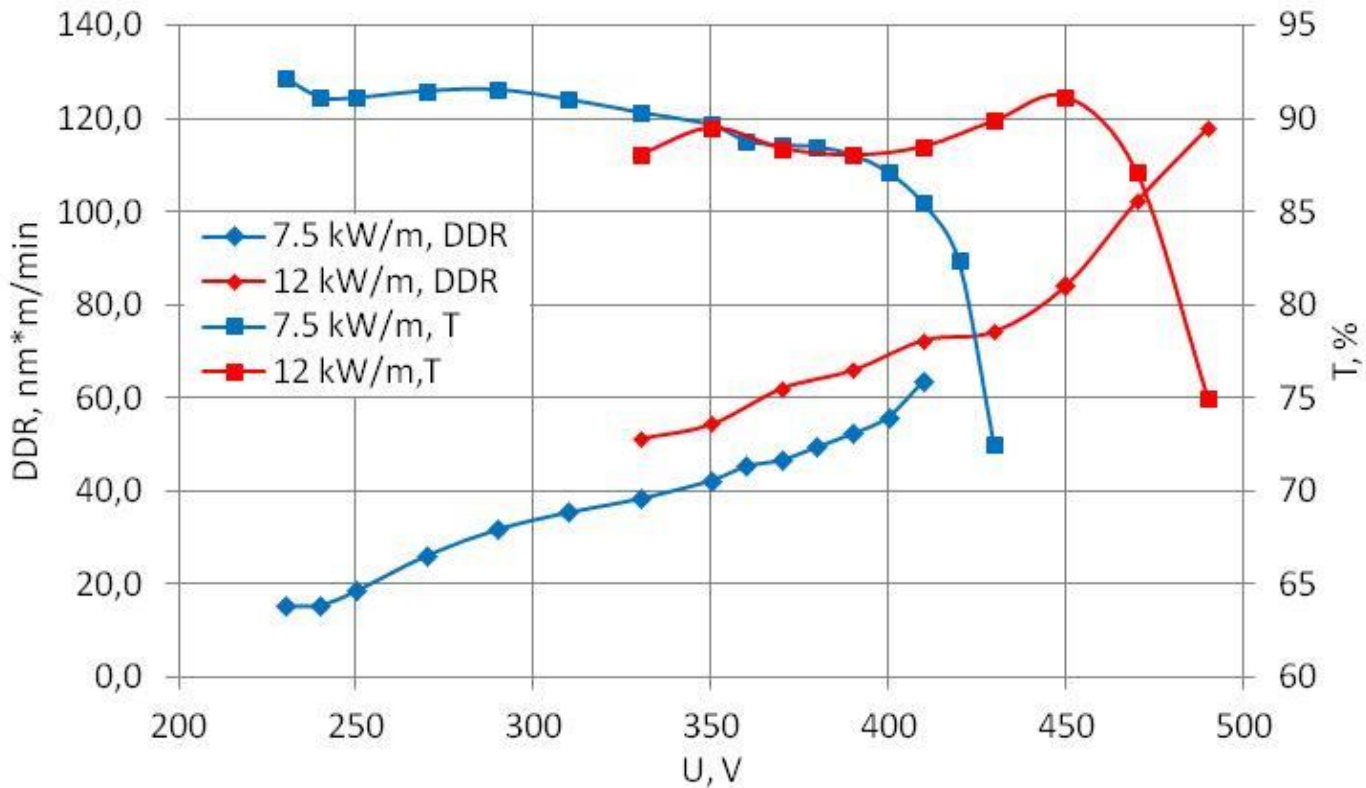


### Parameters

- Main magnetron – Si or Ti
- Auxiliary magnetron – W
- Pressure – 5 mtor
- Distance target-drum – 100 mm
- Rotary magnetron length – 0.66 m
- Auxiliary magnetron length – 0.47 m
- Power supply – pulse DC
- Power (main) – up to 10 kW
- Power (aux) – 0-3 kW
- Substrate speed – 0.2 – 5 m/min

# Reactive process scheme

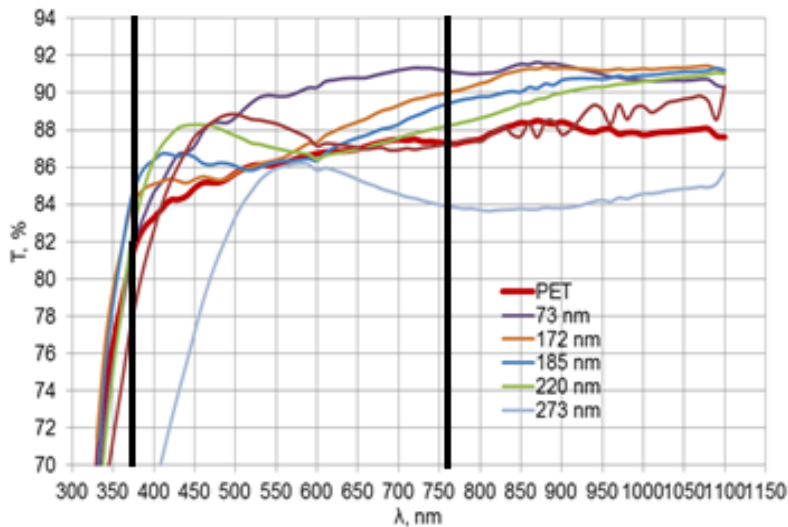




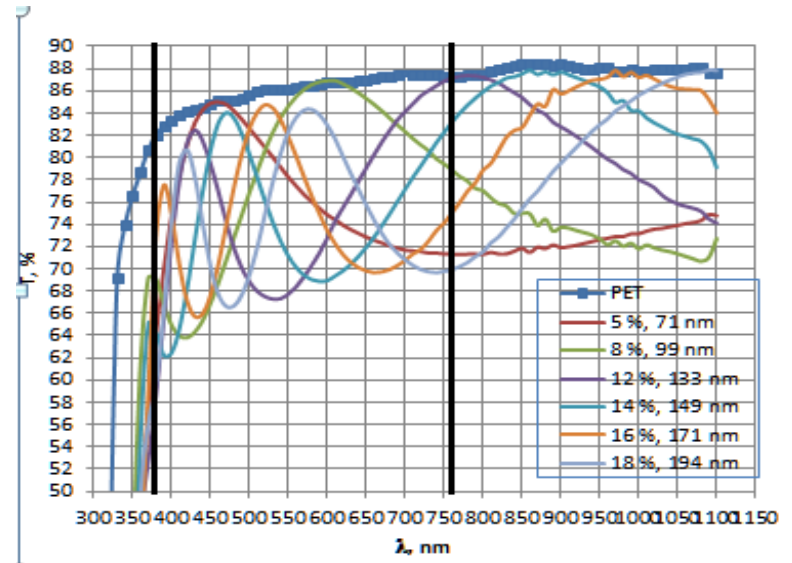
*Comparison of process characteristics and properties of SiO<sub>2</sub> coatings at sputtering power of 7.5 kW/m and 12 kW/m (planar magnetron, pulse power supply).*

# SiO<sub>2</sub> and TiO<sub>2</sub> light transmission spectrums

a) SiO<sub>2</sub>,  $n_{\text{SiO}_2} = 1.48$   
 $n_{\text{PET}} = 1.65$

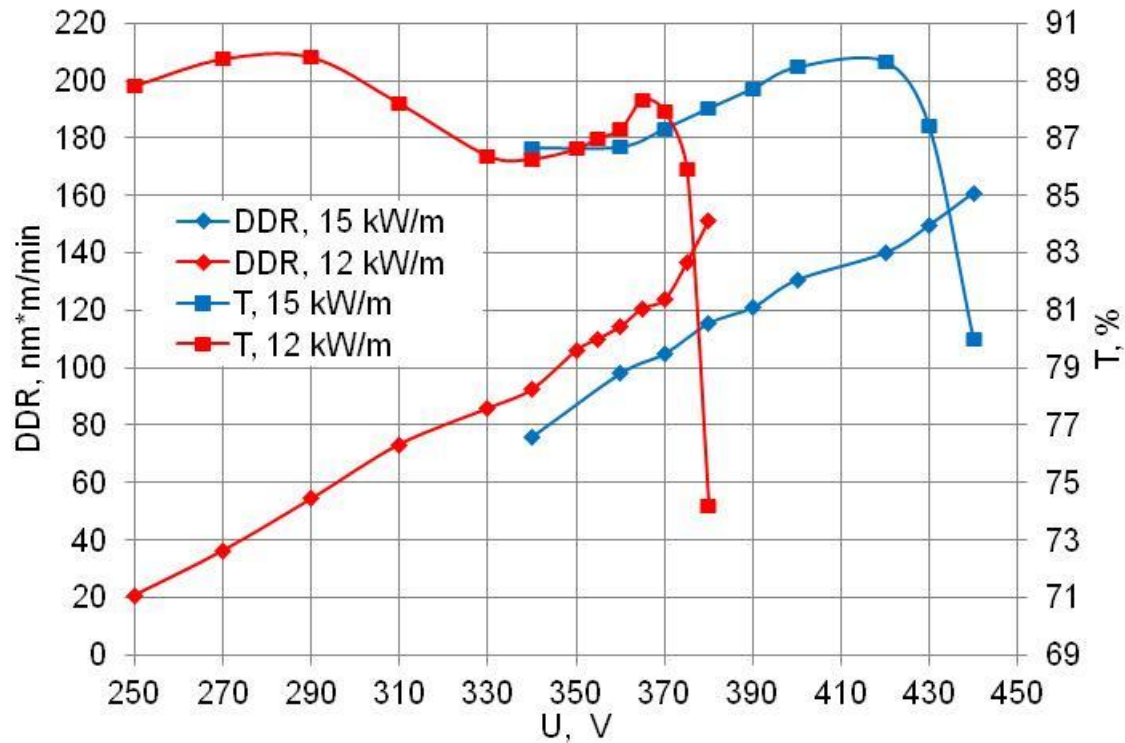


b) TiO<sub>2</sub>,  $n_{\text{TiO}_2} = 2.35$   
 $n_{\text{PET}} = 1.65$

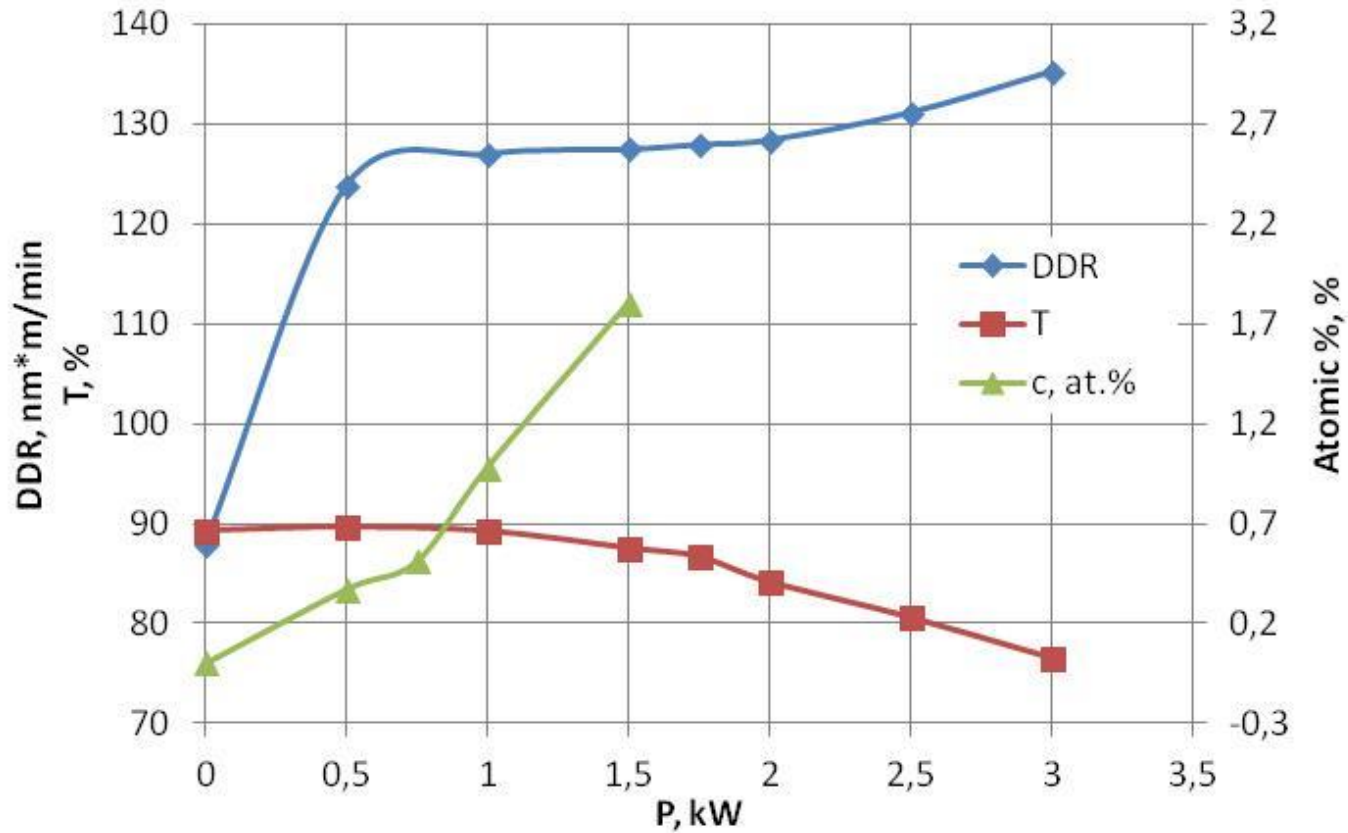


*Transmission spectrum of silicon oxide (a) and titanium oxide (b) coatings of varying thickness produced applying serial co-sputtering*



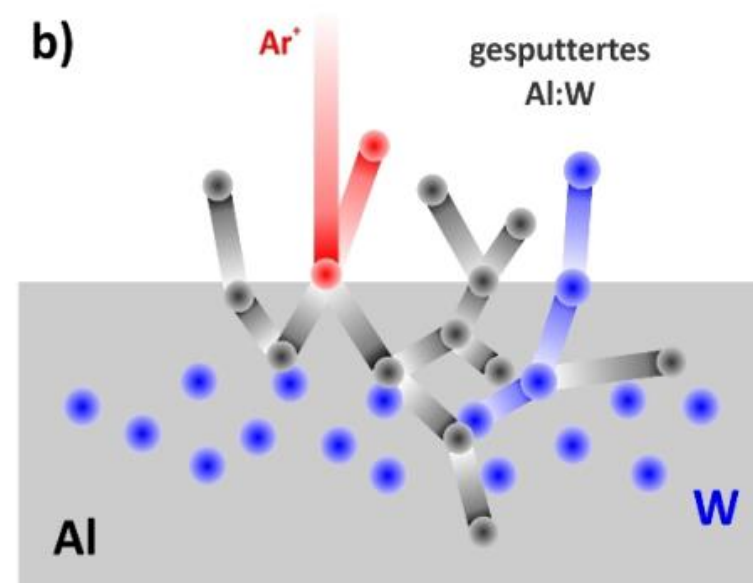
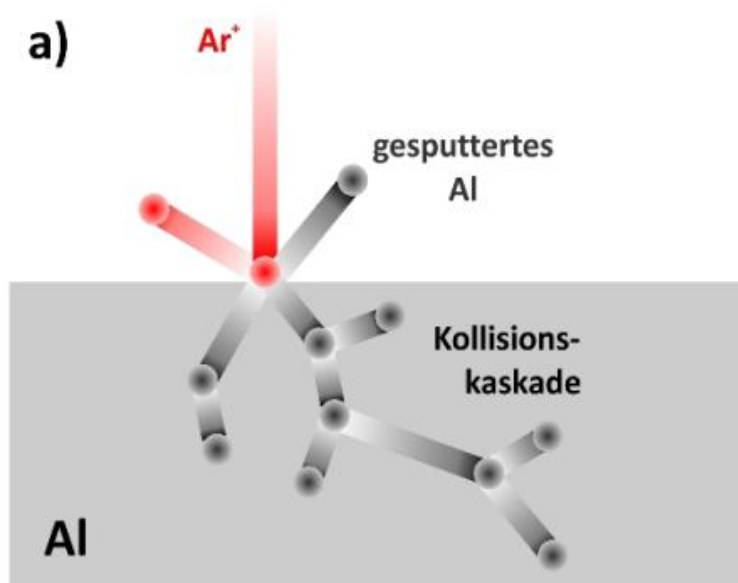


*Comparison of process characteristics and properties of SiO<sub>2</sub> coatings at sputtering power of 12 kW/m and 15 kW/m in a serial co-sputtering process (pulse power supply).*



*Tungsten influence on properties of silicon oxide.*

# The scheme of reflection of cascades of collisions



Michael Austgen. Serielles Co-Sputtern. Düsseldorf, 2011.

# Summary

- Specific power of sputtering, sputtering mode, sputtering factor - the major factors defining DDR.
- Co-sputtering of silicon and tungsten allowed effectively increase DDR for SiO<sub>2</sub> coating (+75%).
- In reactive processes it is recommended to use magnetron pulse power supplies.

**Thanks for your  
attention.**



**CUSTOMIZED VACUUM DEPOSITION  
EQUIPMENT & PROCESSES**

[www.sidrabe.com](http://www.sidrabe.com)

[sidrabe@sidrabe.eu](mailto:sidrabe@sidrabe.eu)